

Radar Pulsed Power Transistor 150W, 2.7-2.9 GHz, 100µs Pulse, 10% Duty

M/A-COM Products Released, 29 Jun 07

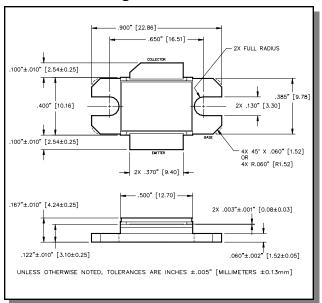
Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- · High efficiency inter-digitized geometry
- · Diffused emitter ballasting resistors
- Gold metallization system
- · Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	65	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	I _C	15.0	Α
Power Dissipation @ +25°C	P _{TOT}	500	W
Storage Temperature	T_{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Outline Drawing



Electrical Specifications: T_C = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I _C = 40mA		BV _{CES}	65	-	V
Collector-Emitter Leakage Current	V _{CE} = 36V		I _{CES}	-	7.5	mA
Thermal Resistance	Vcc = 38V, Pin = 22W	F = 2.7, 2.8, 2.9 GHz	R _{TH(JC)}	-	0.4	°C/W
Output Power	Vcc = 38V, Pin = 22W	F = 2.7, 2.8, 2.9 GHz	P _{OUT}	150	-	W
Power Gain	Vcc = 38V, Pin = 22W	F = 2.7, 2.8, 2.9 GHz	G _P	8.3	=	dB
Collector Efficiency	Vcc = 38V, Pin = 22W	F = 2.7, 2.8, 2.9 GHz	ης	38	i	%
Input Return Loss	Vcc = 38V, Pin = 22W	F = 2.7, 2.8, 2.9 GHz	RL	-	-10	dB
Pulse Droop	Vcc = 38V, Pin = 22W	F = 2.7, 2.8, 2.9 GHz	Droop	-	0.7	dB
Load Mismatch Tolerance	Vcc = 38V, Pin = 22W	F = 2.7, 2.8, 2.9 GHz	VSWR-T	-	2:1	-
Load Mismatch Stability	Vcc = 38V, Pin = 22W	F = 2.7, 2.8, 2.9 GHz	VSWR-S	-	1.5:1	-

Commitment to produce in volume is not guaranteed.

Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available.

Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298
Visit www.macomtech.com for additional data sheets and product information.

[•] Europe Tel: 44.1908.574.200 / Fax: 44.1908.574.300

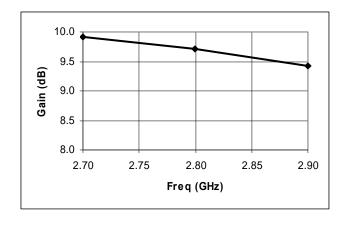


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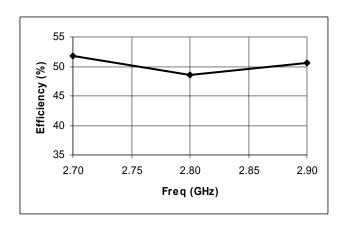
Typical RF Performance

Freq. (GHz)	Pin (W)	Pout (W)	Gain (dB)	Ic (A)	Eff (%)	RL (dB)	Droop (dB)	VSWR-S (1.5:1)	VSWR-T (2:1)
2.7	22	216	9.91	11.0	51.7	-10.9	0.09	S	Р
2.8	22	206	9.71	11.2	48.5	-18.9	0.25	S	Р
2.9	22	193	9.42	10.0	50.5	-10.9	0.12	S	Р

Gain vs. Frequency

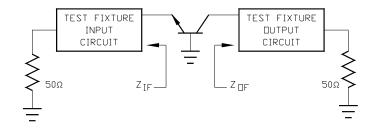


Collector Efficiency vs. Frequency



RF Test Fixture Impedance

F (GHz)	Z _{IF} (Ω)	Z _{OF} (Ω)
2.7	4.6 - j8.3	1.7 - j3.2
2.8	4.1 - j7.8	1.7 - j2.8
2.9	3.7 - j7.5	1.7 - j2.4



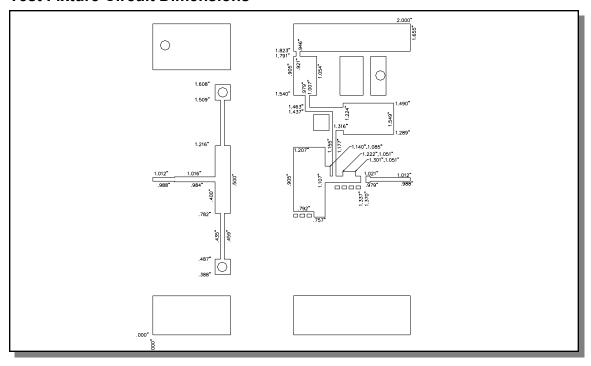
PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed. • **Europe** Tel: 44.1908.574.200 / Fax: 44.1908.574.300

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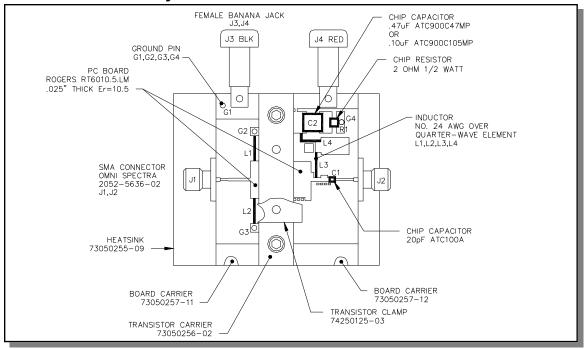


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Test Fixture Circuit Dimensions



Test Fixture Assembly



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